

SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

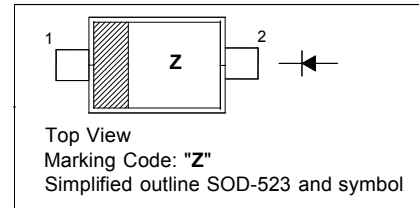
for rectifying small power applications

Features

- Ultra small mold type
- Low forward voltage
- High reliability

PINNING

| PIN | DESCRIPTION |
|-----|-------------|
| 1 | Cathode |
| 2 | Anode |

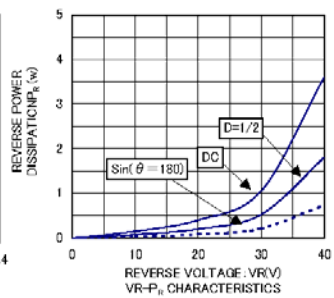
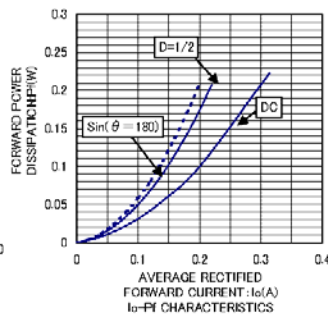
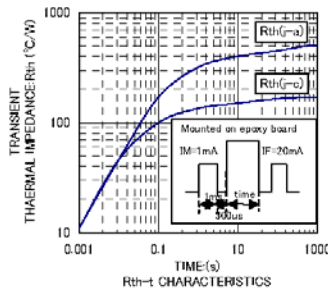
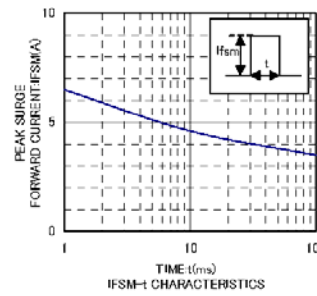
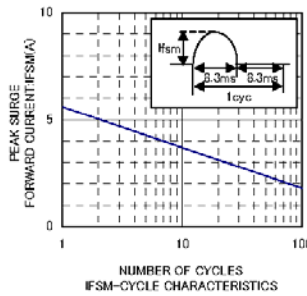
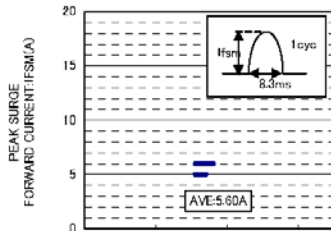
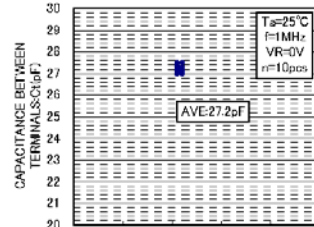
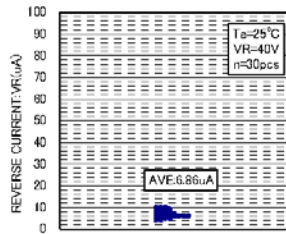
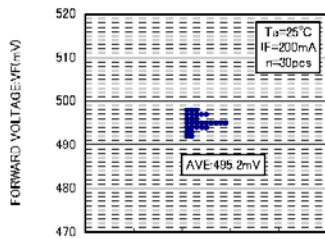
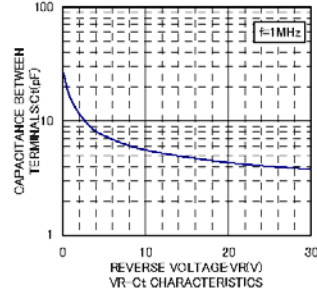
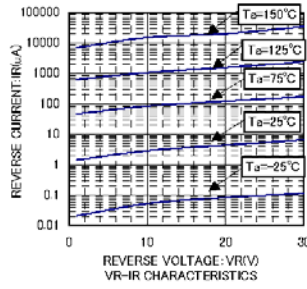
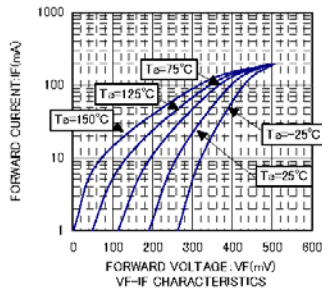


Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

| Parameter | Symbol | Value | Unit |
|--|-----------|---------------|------------------|
| Repetitive Peak Reverse Voltage | V_{RM} | 45 | V |
| Reverse Voltage | V_R | 40 | V |
| Mean Rectifying Current | I_O | 200 | mA |
| Peak Forward Surge Current (60Hz for Cyc.) | I_{FSM} | 1 | A |
| Junction Temperature | T_j | 150 | $^\circ\text{C}$ |
| Storage Temperature Range | T_{stg} | - 55 to + 150 | $^\circ\text{C}$ |

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

| Parameter | Symbol | Min. | Max. | Unit |
|--|--------|----------------------|---------------------|---------------|
| Forward Voltage at $I_F = 10\text{ mA}$ at $I_F = 100\text{ mA}$ at $I_F = 200\text{ mA}$ | V_F | 0.16 0.31 0.41 | 0.3 0.45 0.54 | V |
| Reverse Current at $V_R = 10\text{ V}$ at $V_R = 40\text{ V}$ | I_R | - - | 20 90 | μA |





CHINA BASE
INTERNATIONAL

SOD-523

RB521S-40

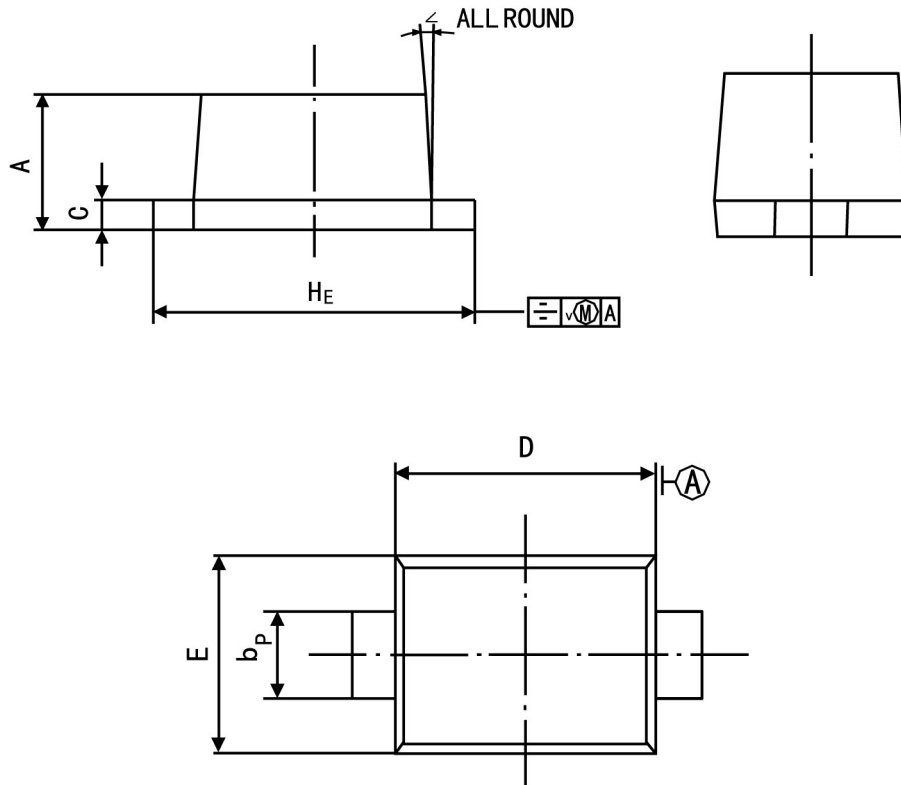


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PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-523



| Symbol | Dimension in Millimeters | |
|--------|--------------------------|------|
| | Min | Max |
| A | 0.60 | 0.70 |
| bp | 0.30 | 0.40 |
| C | 0.100 | 0.14 |
| D | 1.15 | 1.25 |
| E | 0.75 | 0.85 |
| HE | 1.50 | 1.70 |
| V | — | 0.10 |
| ∠ | — | 5° |